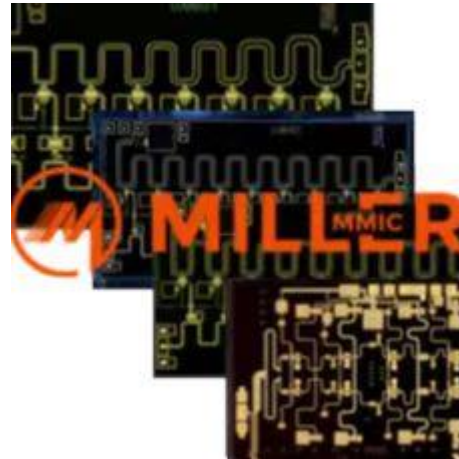


**Features**

- Frequency:DC-20GHz
- Insertion Loss: 0.35dB (typ.)
- Limit Power:14dBm
- Tolerance Power:37dBm(CW)
- Input/Output: 50Ω
- Die Size: 1.42x0.81x 0.1 mm

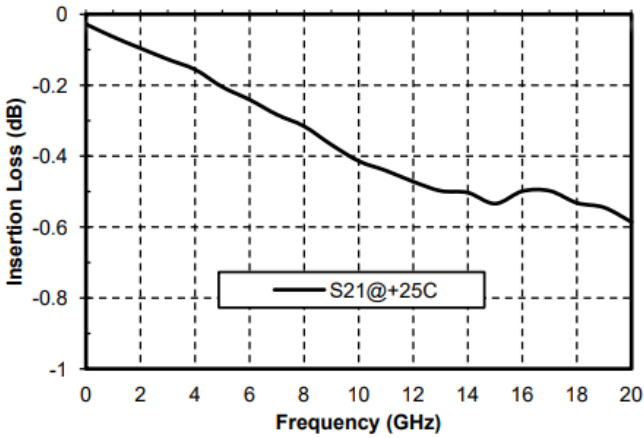

**Typical Applications**

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

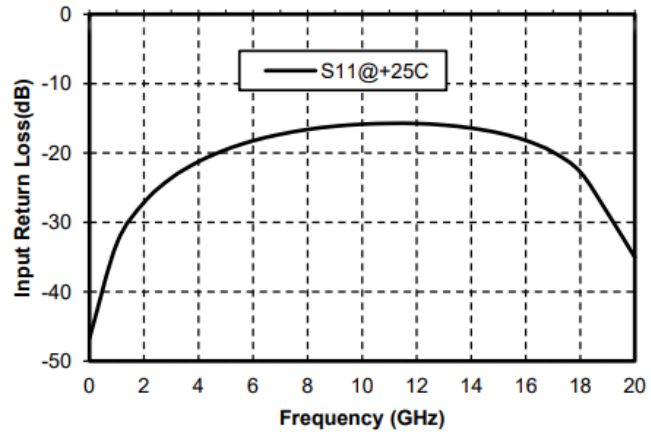
**Electrical Specifications**
**TA = +25°C**

Parameters	Min.	Typ.	Max.	Units
<b>Frequency</b>	<b>DC-20</b>			<b>GHz</b>
<b>Insertion Loss</b>	-	-	<b>0.35</b>	<b>dB</b>
<b>Input Return Loss</b>	-	<b>21</b>	-	<b>dB</b>
<b>Output Return Loss</b>	-	<b>22</b>	-	<b>dB</b>
<b>Limit Power</b>	-	<b>14</b>	-	<b>dBm</b>
<b>Tolerance Power</b>		<b>37</b>		<b>dBm</b>

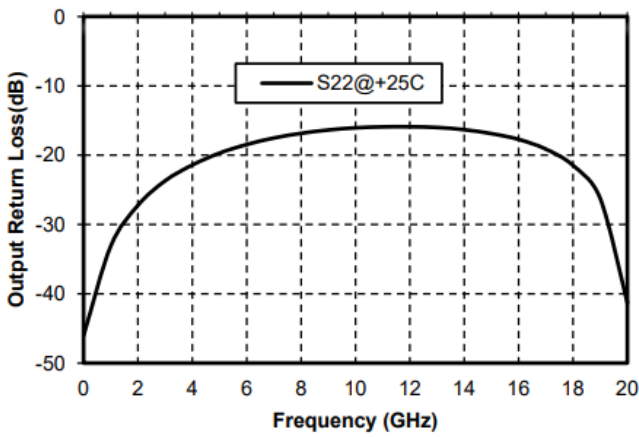
### Insertion Loss Vs. Frequency



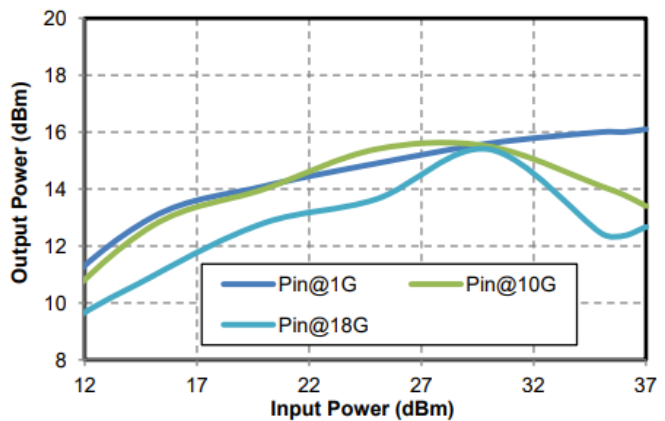
### Input Return Loss Vs. Frequency



### Output Return Loss Vs. Frequency



### Limit Power @1G & 10G 18G





### Outline Drawing:

All Dimensions in  $\mu\text{m}$ , tolerance range  $\pm 50\mu\text{m}$



### Pad Description

PAD	Function	Description
1	RF COMM	RF signal input, external DC-blocking capacitor required.
2	RF OUTPUT	RF signal output, external DC-blocking capacitor required.
Die Bottom	GND	Die bottom must be connected to RF/DC ground.



### Assembly Drawing



#### Notes:

1. Die thickness: 100um
2. Typical bond pad is 100\*100  $\mu\text{m}^2$
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

#### Maximum Ratings:

1. RF input power: +37dBm
2. Storage temperature: -65°C to +150°C
3. Operating temperature: -55°C to 125°C